

NX3020NAKS

30 V, 180 mA dual N-channel Trench MOSFET

11 November 2013

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage	-		-20	-	20	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	180	mA
Static characteristics (per transistor)							
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 100 mA; T_{j} = 25 °C		-	2.7	4.5	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	□6 □5 □4	D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	G1 $G2$ $G2$
4	S2	source TR2	☐1 ☐2 ☐3 (22)	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package	e				
	Name	Description	Version			
NX3020NAKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
NX3020NAKS	Ua%

^[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	180	mA
		V_{GS} = 4.5 V; T_{amb} = 100 °C	[1]	-	110	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	720	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	260	mW
			[1]	-	280	mW
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Symbol	Parameter	Conditions		Min	Max	Unit
		T _{sp} = 25 °C		-	1100	mW
Source-dra	in diode	<u>'</u>	,			,
I _S	source current	T _{amb} = 25 °C		-	180	mA
Per device		<u> </u>	'			
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	375	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

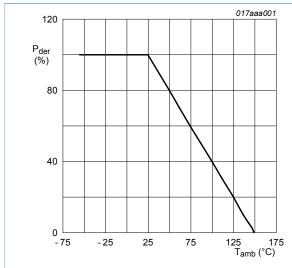


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25\%)}} \times 100\%$$

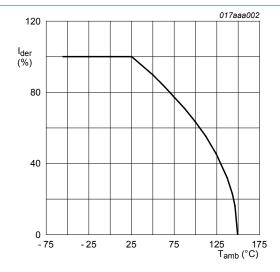


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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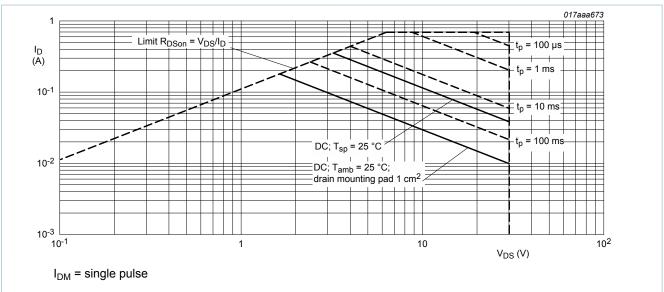


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R _{th(j-a)}	thermal resistance	in free air	[1]	-	390	480	K/W
from junction to ambient	from junction to ambient		[2]	-	380	430	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	110	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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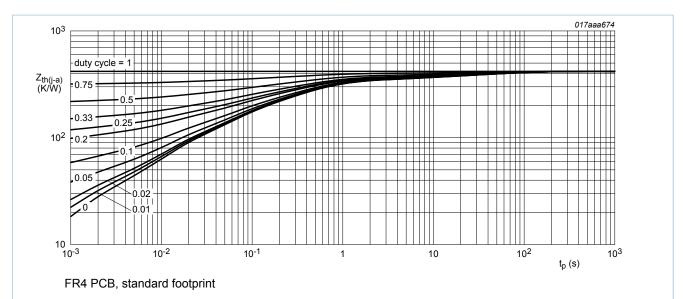
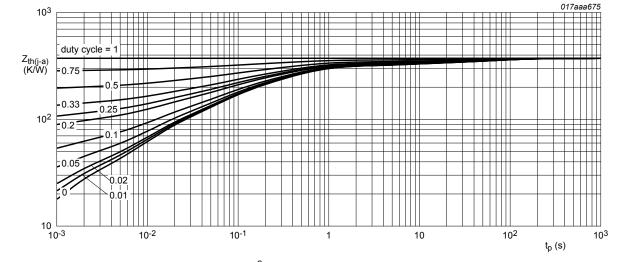


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.8	1.2	1.5	V
I _{DSS} drain leakage curre	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	3.5	μΑ
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	3.5	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μA
	V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	0.5	μA	
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 100 mA; T _j = 25 °C	-	2.7	4.5	Ω
	resistance	V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	5.5	9.2	Ω
		V _{GS} = 4.5 V; I _D = 100 mA; T _j = 25 °C	-	3	5.2	Ω
		V_{GS} = 2.5 V; I_D = 10 mA; T_j = 25 °C	-	4	13	Ω
9fs	forward transconductance	V_{DS} = 10 V; I_D = 150 mA; T_j = 25 °C	-	320	-	mS
Dynamic ch	naracteristics (per transist	or)		'		
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 150 mA; V _{GS} = 4.5 V;	-	0.34	0.44	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.11	-	nC
Q_{GD}	gate-drain charge		-	0.06	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	13	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.6	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R_L = 250 Ω ; V_{GS} = 10 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	34	68	ns
t _f	fall time		-	17	-	ns
Source-drai	in diode (per transistor)			-	'	
V_{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V; T _j = 25 °C	0.47	0.7	1.2	V
		The state of the s	1	1	1	

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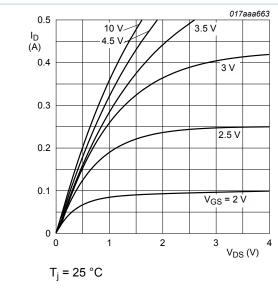


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

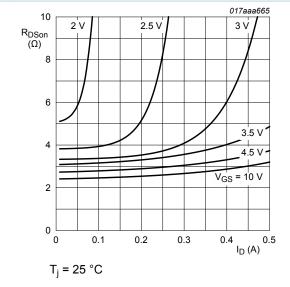


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

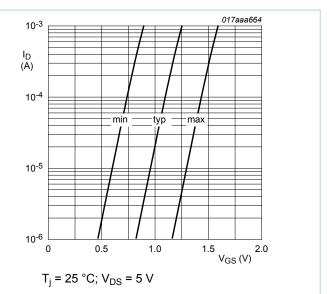


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

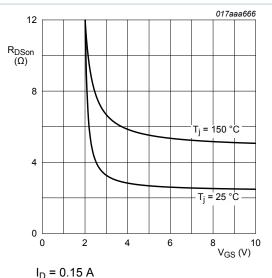


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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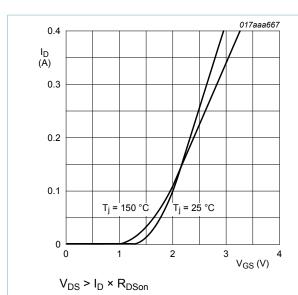


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

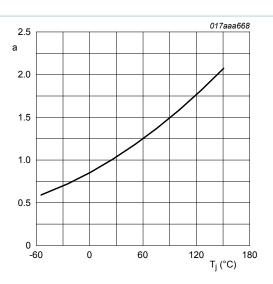


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

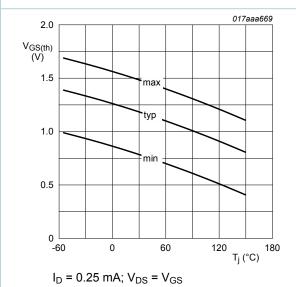
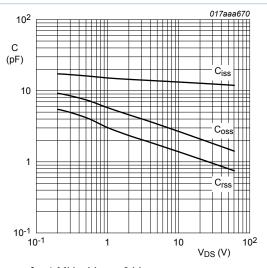


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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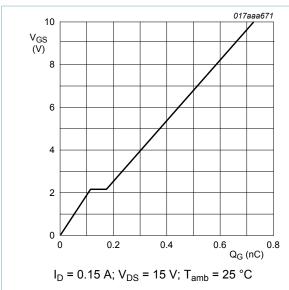


Fig. 14. Gate-source voltage as a function of gate charge; typical values

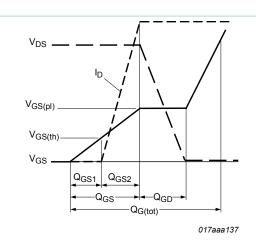


Fig. 15. Gate charge waveform definitions

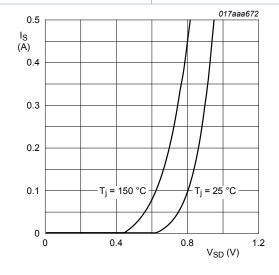
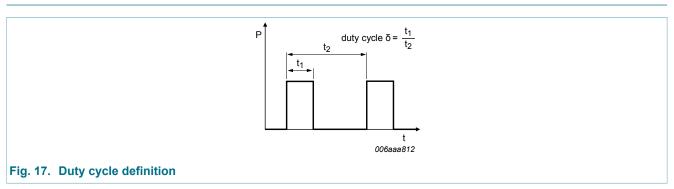


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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12. Package outline

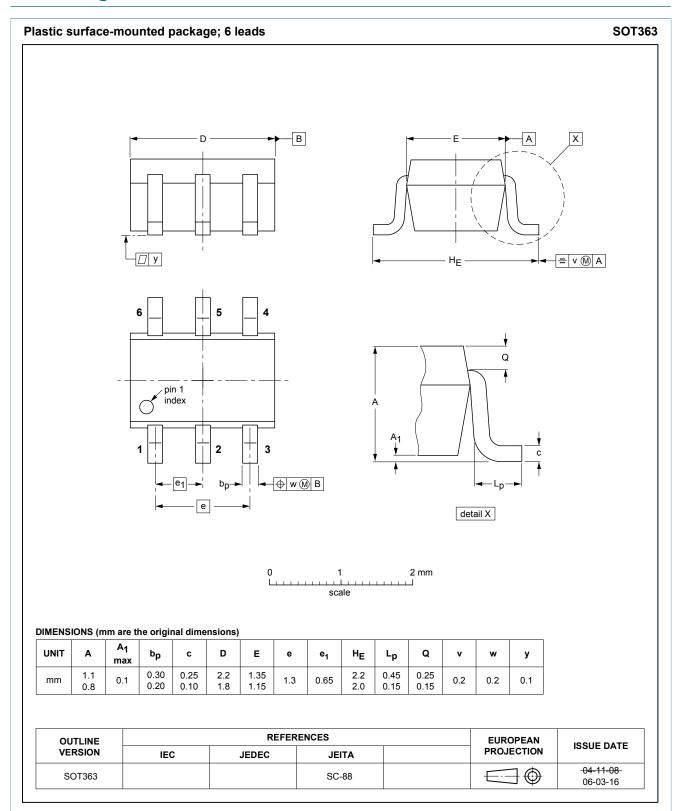
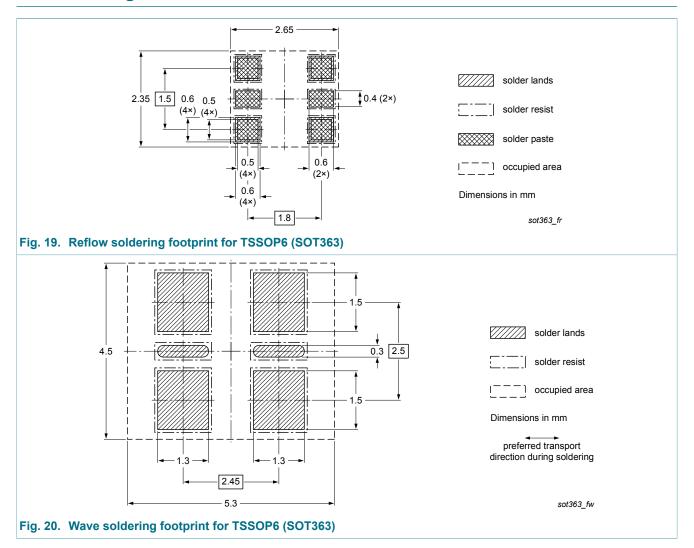


Fig. 18. Package outline TSSOP6 (SOT363)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
NX3020NAKS v.3	20131111	Product data sheet	-	NX3020NAKS v.2			
Modifications:	Marking code corre	Marking code corrected					
NX3020NAKS v.2	20131029	Product data sheet	-	NX3020NAKS v.1			
NX3020NAKS v.1	20120706	Product data sheet	-	-			

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15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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